# **High Current Transistors NPN Silicon**

COLLECTOR

2

BASE

1

EMITTER

#### **MAXIMUM RATINGS**

Rating	Symbol	BC 635	BC 637	BC 639	Unit
Collector-Emitter Voltage	VCEO	45	60	80	Vdc
Collector-Base Voltage	V <sub>СВО</sub>	45 60 8		80	Vdc
Emitter-Base Voltage	VEBO	5.0		Vdc	
Collector Current — Continuous	IC	0.5		Adc	
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	625 5.0		mW mW/°C	
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	1.5 12		Watt mW/°C	
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150		°C	

## BC637 BC639

**BC635** 



### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

## $\textbf{ELECTRICAL CHARACTERISTICS} \ (T_{A} = 25^{\circ}\text{C unless otherwise noted})$

Characteristic		Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS							
Collector-Emitter Breakdown Voltage <sup>(1)</sup> (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 0)	BC635 BC637 BC639	V(BR)CEO	45 60 80		_ _ _	Vdc	
Collector-Base Breakdown Voltage (I <sub>C</sub> = 100 μAdc, I <sub>E</sub> = 0)	BC635 BC637 BC639	V(BR)CBO	45 60 80	_ _ _	_ _ _	Vdc	
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 10 μAdc, I <sub>C</sub> = 0)		V(BR)EBO	5.0		_	Vdc	
Collector Cutoff Current $(V_{CB} = 30 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 30 \text{ Vdc}, I_E = 0, T_A = 125^{\circ}\text{C})$		ICBO	_ _ _		100 10	nAdc μAdc	

<sup>1.</sup> Pulse Test: Pulse Width  $\leq 300~\mu s,$  Duty Cycle 2.0%.



### BC635 BC637 BC639

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS <sup>(1)</sup>						
DC Current Gain (I <sub>C</sub> = 5.0 mAdc, $V_{CE}$ = 2.0 Vdc) (I <sub>C</sub> = 150 mAdc, $V_{CE}$ = 2.0 Vdc) (I <sub>C</sub> = 500 mA, $V_{CE}$ = 2.0 V)	BC635 BC637 BC639	hFE	25 40 40 40 40 25			_
Collector-Emitter Saturation Voltage (IC = 500 mAdc, IB = 50 mAdc)		VCE(sat)	_	_	0.5	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 2.0 Vdc)		VBE(on)	_	_	1.0	Vdc
DYNAMIC CHARACTERISTICS						
Current-Gain — Bandwidth Product (IC = 50 mAdc, VCE = 2.0 Vdc, f = 100 MHz)		fΤ	_	200	_	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)		C <sub>ob</sub>	_	7.0	_	pF
Input Capacitance (VEB = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)		C <sub>ib</sub>	_	50	_	pF

<sup>1.</sup> Pulse Test: Pulse Width  $\leq 300~\mu s,$  Duty Cycle 2.0%.

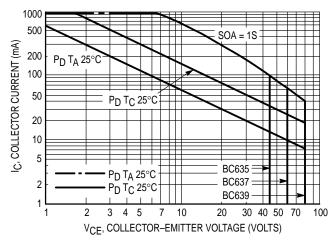


Figure 1. Active Region Safe Operating Area

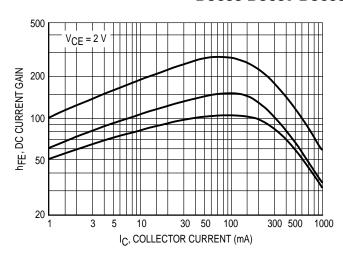


Figure 2. DC Current Gain

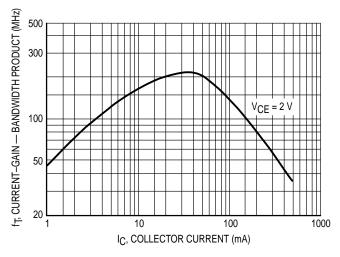


Figure 3. Current-Gain — Bandwidth Product

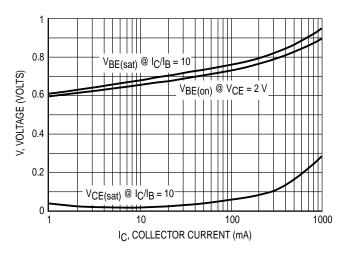
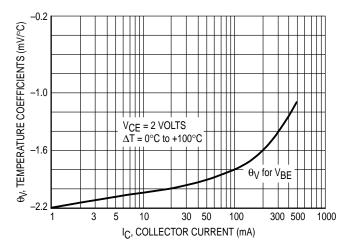
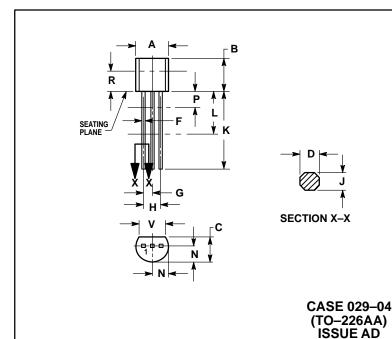


Figure 4. "Saturation" and "On" Voltages



**Figure 5. Temperature Coefficients** 

#### PACKAGE DIMENSIONS



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
  CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN P AND L. DIMENSION F APPLIES BETWEEN F AIND L.
  DIMENSION D AND J APPLY BETWEEN L AND K
  MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIMETERS			
DIM	MIN	MAX	MIN	MAX		
Α	0.175	0.205	4.45	5.20		
В	0.170	0.210	4.32	5.33		
С	0.125	0.165	3.18	4.19		
D	0.016	0.022	0.41	0.55		
F	0.016	0.019	0.41	0.48		
G	0.045	0.055	1.15	1.39		
Н	0.095	0.105	2.42	2.66		
J	0.015	0.020	0.39	0.50		
K	0.500		12.70			
L	0.250		6.35			
N	0.080	0.105	2.04	2.66		
Р		0.100	_	2.54		
R	0.115		2.93			
V	0.135		3 43			

STYLE 14:

PIN 1. EMITTER

COLLECTOR BASE

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